

5

ABSTRACT

10 A method used to form a semiconductor device having a capacitor
comprises placing a semiconductor wafer assembly into a chamber of a plasma
source, the wafer assembly comprising a layer of insulation having at least one
contact therein and a surface, and further comprising a conductive layer over the
surface and in the contact. Next, in the chamber, a layer of etch resistant
material is formed within the contact over the conductive layer, the etch resistant
material not forming over the surface.

15

00470650-43300